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#### **ABSTRACT OF THE DISCLOSURE**

A method of forming a CMOS TFT device. The present method features that the  $n^+$ -ion doping procedure is performed after defining the contact holes located in the doped areas. Thus,  
5 the source/drain region of the NMOS can be formed. The present invention requires only five photomasks, thereby reducing the number of photomasks consumed in the prior art.